

## CLAIMS

1. A ceramic substrate, for a semiconductor producing/examining device, having a conductor formed inside  
5 thereof or on the surface thereof,  
wherein said ceramic substrate has been sintered such that a fractured section thereof exhibits intergranular fracture.
2. The ceramic substrate for a semiconductor  
10 producing/examining device according to claim 1,  
wherein an average diameter of ceramic grains of said fractured section is 0.5 to 10  $\mu\text{m}$ .
3. The ceramic substrate for a semiconductor  
15 producing/examining device according to claim 1,  
wherein an impurity element is locally distributed in boundaries of ceramic grains of said fractured section.
4. The ceramic substrate for a semiconductor  
20 producing/examining device according to claim 1,  
wherein thermal conductivity of said ceramic substrate is 100 W/m $\cdot$ K or more.
5. The ceramic substrate for a semiconductor  
25 producing/examining device according to claim 1,  
wherein said ceramic substrate is constituted such that:  
an impurity-existent area where an impurity element is locally distributed in triple points of crystal grains, and  
an impurity element-nonexistent area where an impurity  
30 is not locally distributed in the triple points of the crystal grains,  
coexist therein.

FOR INFORMATION  
DISCLOSURE  
PURPOSES ONLY

Related Pending Application

Related Case Serial No: 10/259,083

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